

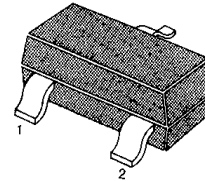
BC807/BC808**PNP EPITAXIAL SILICON TRANSISTOR****SWITCHING AND AMPLIFIER APPLICATIONS**

- Suitable for AF-Driver stages and low power output stages
- Complement to BC817/BC818

ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)

Characteristic	Symbol	Rating	Unit
Collector Emitter Voltage :BC807	V _{CES}	-50	V
:BC808		-30	V
Collector Emitter Voltage :BC807	V _{CEO}	-45	V
:BC808		-25	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-800	mA
Collector Dissipation	P _C	-310	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-65 ~ 150	°C

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_A=25 °C)

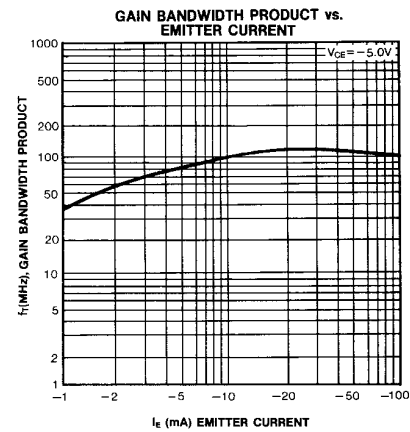
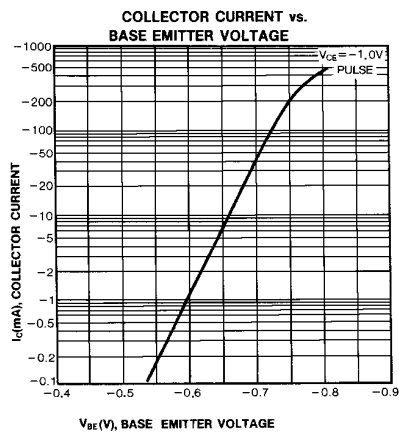
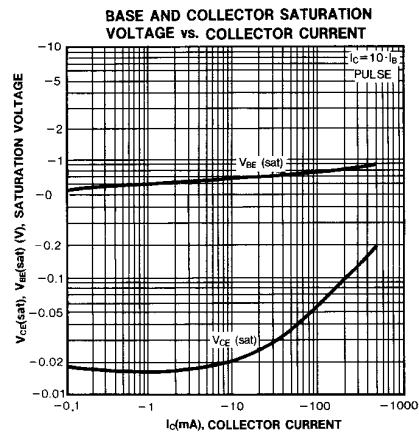
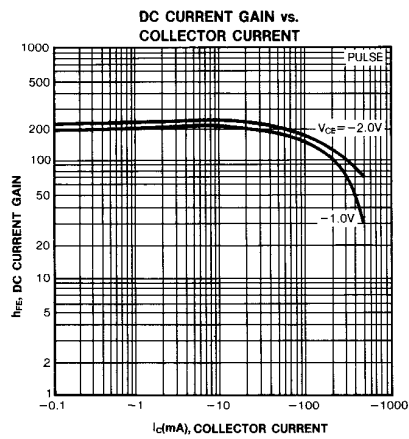
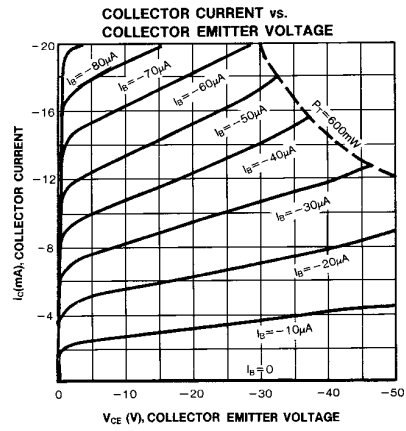
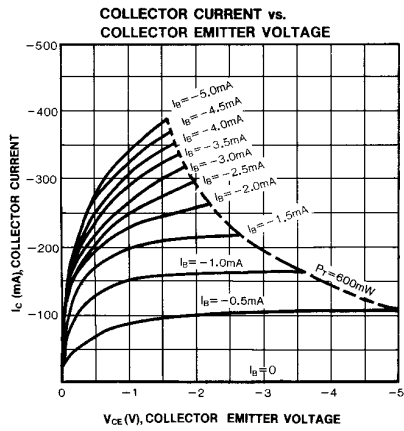
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage :BC807	BV _{CEO}	I _C = -10mA, I _B =0	-45			V
:BC808			-25			V
Collector-Emitter Breakdown Voltage :BC807	BV _{CES}	I _C = -0.1mA, I _B =0	-50			V
:BC808			-30			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -0.1mA, I _C =0	-5			V
Collector Cut-off Current	I _{CES}	V _{CE} = -25V, I _B =0			-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -4V, I _C =0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} = -1V, I _C = -100mA	100		630	
	h _{FE2}	V _{CE} = -1V, I _C = -300mA	60			
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -500mA, I _B = -50mA			-0.7	V
Base-Emitter On Voltage	V _{BE} (on)	V _{CE} = -1V, I _C = -300mA			-1.2	V
Current Gain Bandwidth Product	f _T	V _{CE} = -5V, I _C = -10mA f=50MHz		100		MHz
Collector-Base Capacitance	C _{CBO}	V _{CB} = -10V, f=1MHz			12	pF

h_{FE} CLASSIFICATION

Classification	16	25	40
h _{FE1}	100-250	160-400	250-630
h _{FE2}	60-	100-	170-

MARKING CODE

TYPE	807-16	807-25	807-40	808-16	808-25	808-40
MARKING	9FA	9FB	9FC	9GA	9GB	9GC



BC807/BC808

PNP EPITAXIAL SILICON TRANSISTOR

